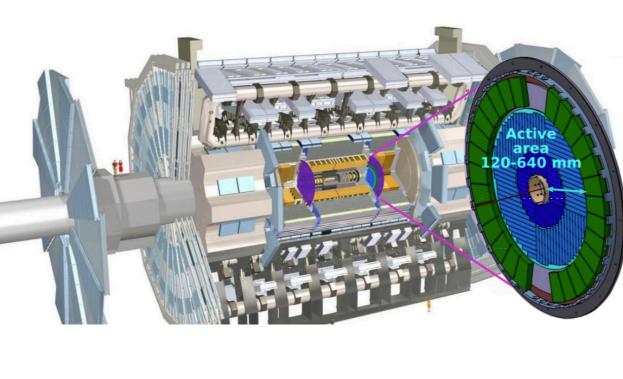


Study of total ionization does effects on IHEP-NDL LGAD sensors

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Introduction

- Low Gain Avalanche Detectors (LGAD) was developed to achieve high time resolution (30ns) to solve the pile up problem for for the ATLAS Phase-II upgrade.
- To operate in the harsh environment in high luminosity LHC, the LGAD sensor should be radiation hardness. This

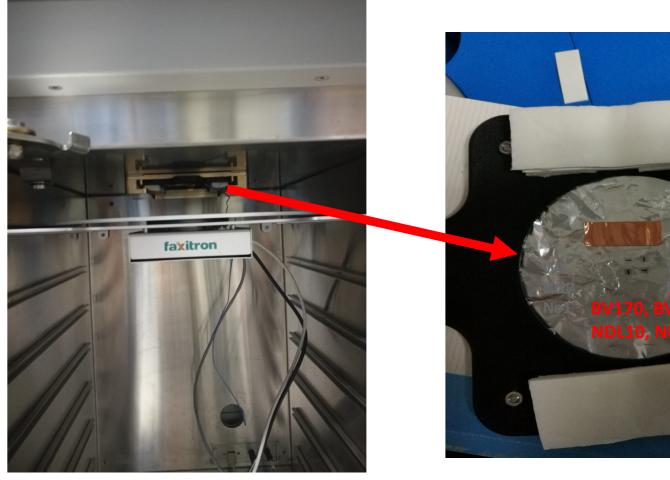


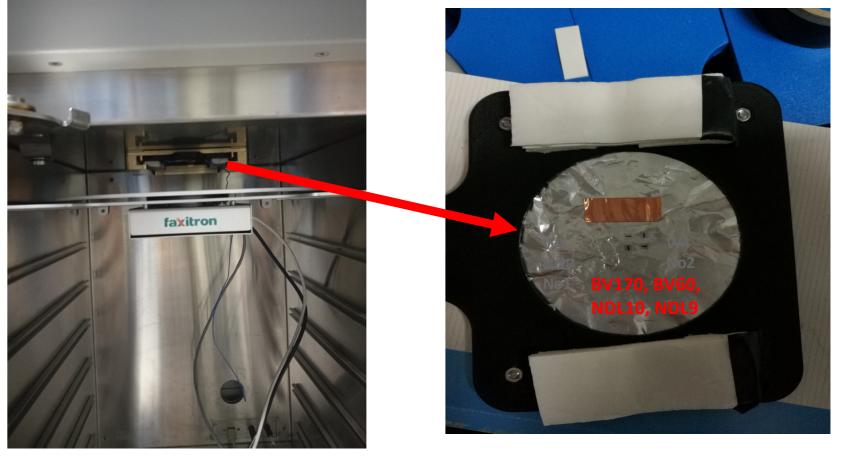


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TID test setup

- LGAD sensors were irradiated with MutiRad 160.
 - –Dose rate: 174.5Gy/min
 - –Filter: 0.09mm Al
 - -Dose: 0, 1kGy, 10kGy, 100kGy



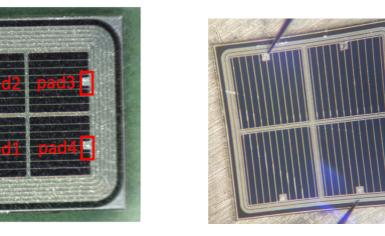


- contribution focuses on total icrization does (TID) effects on LGAD sensors developed by NDL (Novel Device Laboratory) and IHEP.
- 2x2 LGAD sensor with different doping profile, epitaxial resistance and guardring design were irradiated to 100kGy by MultiRad 160. The changes of key parameters of LGAD after x-ray irradiation were measured.

Property of NDL sensor

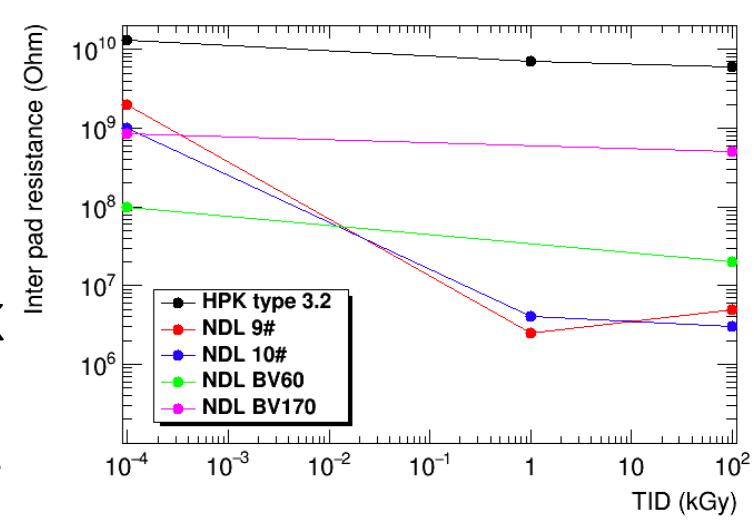
LGAD has a highly p-doped multiplication layer at the np-junction to obtain the high gain and high time precision.

IHEP-NDL designed four kinds of LGAD sensor.



After irradiation: Inter-pad resistance

NDL 2x2 sensors : 6GR design has better Inter-pad resistance than 2GR design after irradiation. Compared with HPK 3.2 (5x5): HPK showed better interpad isolation after irradiation.



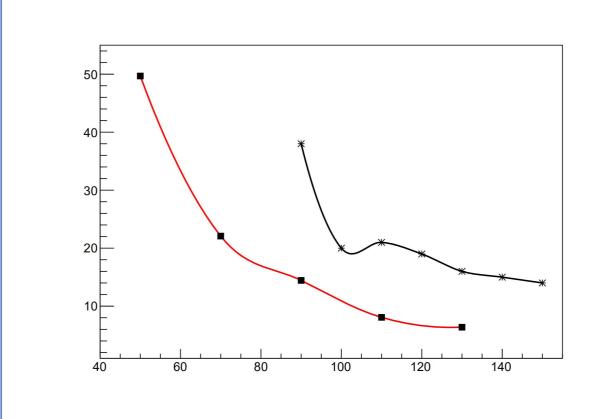
			BV170& BV60 NDL 9	
LGAD	High resistance silicon	Low resistance silicon	Number of Guard Ring	Guard Ring with metal contact
NDL1810-2-9	No	Yes	2	Yes
NDL1810-2-10	No	Yes	2	Yes
BV60	No	Yes	6	No
BV170	Yes	No	6	No

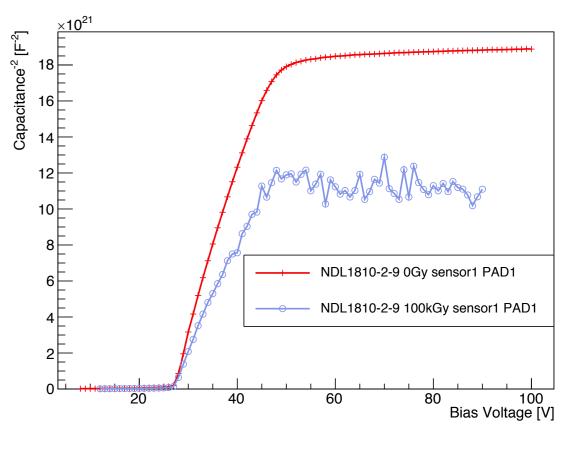
After irradiation: IV — leakage current and breakdown

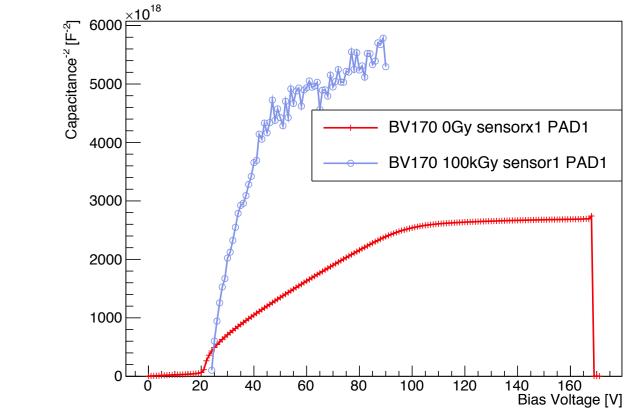
After 100kGy NDL1810-2-9 sensor1 0Gy NDL1810-2-10 sensorx2 0Gy 10 10 NDL1810-2-9 sensor1 100kG NDL1810-2-10 sensor3 100kGy irradiation, the leakage currents of $\frac{1}{2}$ 10-1 10⁻⁸ the IHEP-NDL LGAD sensor decrease. The NDL1810-2-10 Bias Voltage [V Bias Voltage [V has the smallest BV60 sensor4 0Gy BV170 sensorx 0Gy 10⁻² 10⁻⁴ 10⁻³ leakage current. BV60 sensor2 100kGy BV170 sensor2 100kGy 10⁻⁴

After irradiation: CV and timeresolution

After 100kGy irradiation, fully depleted voltage was slightly increase except NDL1810-2-10.

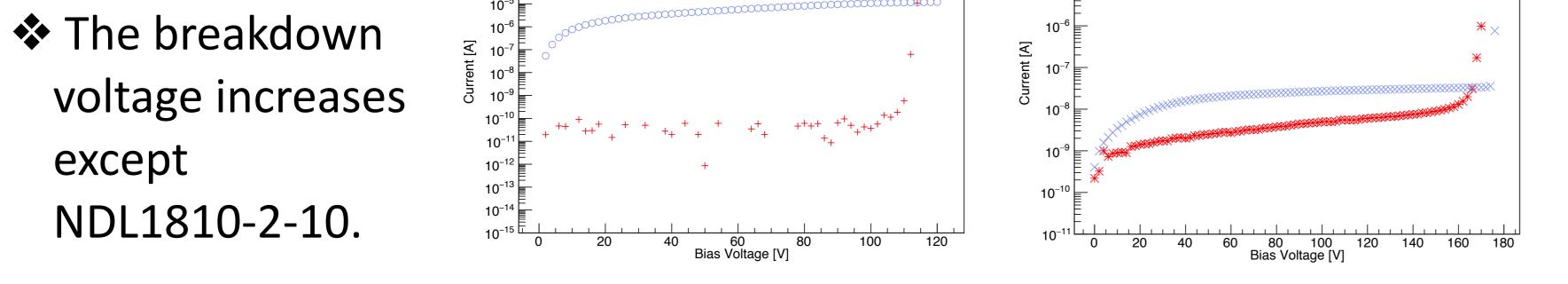






Conclusion: 1

Leakage current of NDL1810-2-10 is better than the



Conclusion: 2

The guard ring design could improve the inter-pad isolation and the TID hardness irradiation;

High resistance silicon could improve the depletion performance.

other sensors even compared with HPK sensors(T3.1, T3.2).

